

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

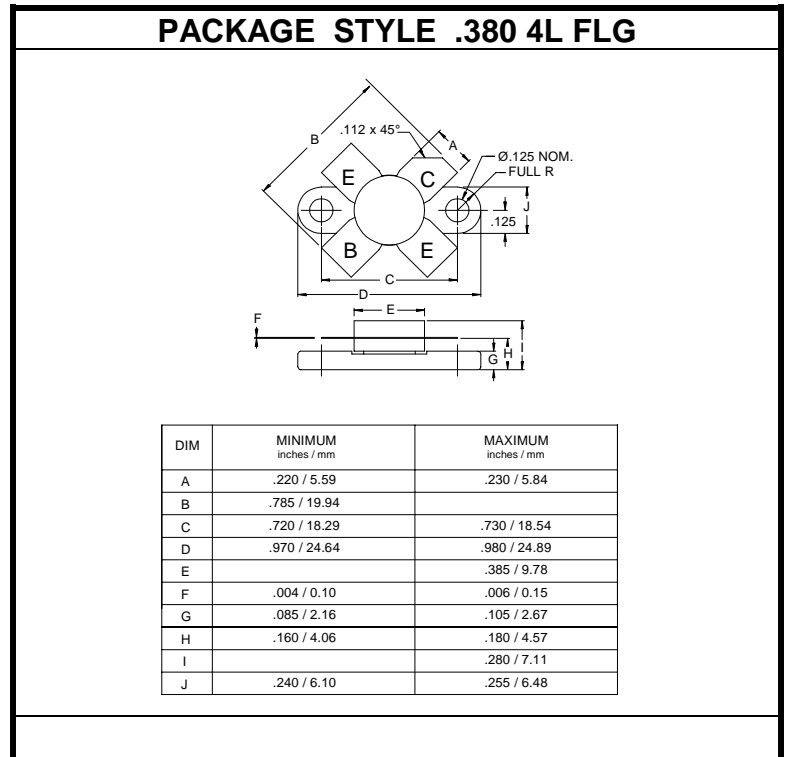
The **ASI BLV20** is Designed for Class C, 28 V High Band Applications up to 175 MHz.

FEATURES:

- Common Emitter
- $P_G = 12$ dB at 8.0 W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	1.0 A
V_{CB0}	65 V
V_{CEO}	35 V
V_{CES}	65 V
V_{EBO}	4.0 V
P_{DISS}	20 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150°C
θ_{JC}	8.75 °C/W


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	$I_C = 200$ mA	65			V
BV_{CES}	$I_C = 2.0$ mA	65			V
BV_{CEO}	$I_C = 10$ mA	35			V
BV_{EBO}	$I_E = 1.0$ mA	4.0			V
I_{CB0}	$V_{CB} = 36$ V			1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 400$ mA	10		100	---
C_C	$V_{CB} = 28$ V $f = 1.0$ MHz		10		pF
P_G η_c	$V_{CC} = 28$ V $P_{OUT} = 8.0$ W $f = 175$ MHz	12	60		dB %